International Conference Micro- and Nano-Electronics 2012

Alexander A. Orlikovsky
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Contents

xi Conference Committee
xvii Introduction

SESSION 1 PLASMA AND THERMAL PROCESSING

8700 02 Formation of nanoscale structures by inductively coupled plasma etching [8700-45]
C. C. Welch, Oxford Instruments (United Kingdom); D. L. Olynick, Z. Liu, Lawrence Berkeley National Lab. (United States); A. Holmberg, Royal Institute of Technology (Sweden); C. Peroz, aBeam Technologies, Inc. (United States); A. G. Robinson, The Univ. of Birmingham (United Kingdom); M. D. Henry, Sandia National Labs. (United States); A. Scherer, California Institute of Technology (United States); T. Mollenhauer, AMO GmbH (Germany); V. Genova, Cornell Univ. (United States); D. K. T. Ng, A*STAR - Data Storage Institute (Singapore)

8700 03 The effects of additive gases (Ar, N₂, H₂, Cl₂, O₂) on HCl plasma parameters and composition [8700-28]
A. Efremov, A. Yudina, A. Davlyatshina, D. Murin, V. Svetlov, Ivanovo State Univ. of Chemistry and Technology (Russian Federation)

8700 04 Instrumented wafer as a Langmuir multiprobe tool for lateral plasma homogeneity measurements in processing plasma reactors [8700-44]
A. Miakonkikh, S. Lisovsky, M. Rudenko, K. Rudenko, Institute of Physics and Technology (Russian Federation)

8700 05 Copper germanium alloys formation by the low temperature atomic hydrogen treatment [8700-8]
A. I. Kazimirov, Tomsk State Univ. of Control Systems and Radioelectronics (Russian Federation); E. V. Erofeev, V. A. Kagadel, Micran (Russian Federation)

8700 06 Temperature oscillations in a silicon wafer under constant power of incoherent irradiation by heating lamps in a thermal chamber of RTP set up [8700-53]
V. I. Rudakov, A. L. Kurenya, V. V. Ovcharov, V. P. Prigara, Institute of Physics and Technology, Yaroslavl Branch (Russian Federation)
SESSION 2  MICRO- AND NANOELECTRONIC STRUCTURES

8700 07  Influence of metamorphic buffer design on electrophysical and structural properties of 
MHEMT nanoheterostructures In$_{0.7}$Al$_{0.3}$As/In$_{0.7}$Ga$_{0.3}$As/In$_{0.7}$Al$_{0.3}$As/GaAs [8700-33]  
S. S. Pushkarev, Institute of UHF Semiconductor Electronics (Russian Federation) and 
National Research Nuclear Univ. MEPhI (Russian Federation); G. B. Galiev, E. A. Klimov, 
D. V. Lavrukhin, Institute of UHF Semiconductor Electronics (Russian Federation); 
I. S. Vasil'evskii, Institute of UHF Semiconductor Electronics (Russian Federation) and 
National Research Nuclear Univ. MEPhI (Russian Federation); R. M. Imamov, I. A. Subbotin, 
O. M. Zhigalina, V. G. Zhigalina, A.V. Shubnikov Institute of Crystallography (Russian 
Federation); P. A. Buffat, B. Dwir, Ecole Polytechnique Fédérale de Lausanne (Switzerland); 
E. I. Suvorova, A.V. Shubnikov Institute of Crystallography (Russian Federation) and 
Ecole Polytechnique Fédérale de Lausanne (Switzerland)

8700 08  Laser pulse crystallization and optical properties of Si/SiO$_2$ and Si/Si$_3$N$_4$ multilayer nano- 
 heterostructures [8700-6]  
V. A. Voladin, A.V. Rzhanov Institute of Semiconductor Physics (Russian Federation); 
S. A. Arzhannikova, A. A. Gismatulin, G. N. Kamaev, A. K. Antonenko, S. G. Cherkova, 
A. G. Cherkov, A.V. Rzhanov Institute of Semiconductor Physics (Russian Federation) and 
Novosibirsk State Univ. (Russian Federation); S. A. Kochubei, A.V. Rzhanov Institute of 
Semiconductor Physics (Russian Federation); A. A. Popov, Yaroslavl Dept. of IPT (Russian 
Federation); S. Robert, H. Rinnert, M. Vergnat, Institut Jean Lamour, CNRS, Nancy Univ. 
(France)

8700 09  Effect of nanodimensional polyethylenimine layer on surface potential barriers of hybrid 
structures based on silicon single crystal [8700-22]  
I. V. Malyar, D. A. Gorin, S. V. Stetsyura, N.G. Chernyshevsky Saratov State Univ. (Russian 
Federation)

8700 0A  Formation of carbon nanotubes-silicon composite structure for high capacity battery 
electrode [8700-49]  
E. P. Kitsyuk, National Research Univ. of Electronic Technology (Russian Federation); 
V. A. Galperin, Y. P. Shaman, Scientific-Manufacturing Complex "Technological Ctr." 
(Russian Federation); D. G. Gromov, National Research Univ. of Electronic Technology 
(Russian Federation); A. M. Skundin, E. K. Tuseeva, A.N. Frumkin Institute of Physical 
Chemistry and Electrochemistry (Russian Federation)

8700 0B  Formation of nanoelectrodes for high temperature single-electron sensors [8700-31]  
A. A. Parshintsev, E. S. Soldatov, Moscow State Univ. (Russian Federation)

8700 0C  Fabrication of integrated electrodes of molecular transistor by lithographic techniques and 
electromigration [8700-27]  
A. S. Stepunov, E. S. Soldatov, O. V. Snigirev, Moscow State Univ. (Russian Federation)

8700 0D  High-resolution X-ray diffraction and electron microscopy study of porous GaAs substrates 
[8700-19]  
A. A. Lomov, Institute of Physics and Technology (Russian Federation); J. Grym, 
D. Nohavica, Institute of Photonics and Electronics of the ASCR, v.v.i. (Czech Republic); 
A. S. Orekov, A. L. Vasiliev, Russian Research Ctr. Kurchatov Institute (Russian Federation); 
D. V. Novikov, Deutsches Elektronen-Synchrotron (Germany)
Features of formation of high-k dielectric layer in w/ultrathin HfO_2/Si (100) structures under annealing [8700-54]
V. I. Rudakov, E. A. Bogoyavlenskaya, Y. I. Denisenko, V. V. Naumov, Institute of Physics and Technology, Yaroslavl Branch (Russian Federation)

SESSION 3 MAGNETIC AND SUPERCONDUCTING STRUCTURES

Thermodynamics of antiferromagnetic nanoparticles and macroscopic quantum effects observed by Mössbauer spectroscopy [8700-11]
M. A. Chuev, Institute of Physics and Technology (Russian Federation)

Characterization of nanoparticles in a media using multilevel models of magnetic dynamics [8700-35]
I. Mischenko, M. Chuev, Institute of Physics and Technology (Russian Federation); V. Cherepanov, M. Polikarpov, V. Panchenko, Russian Research Ctr. Kurchatov Institute (Russian Federation)

Field-induced transitions in ferrimagnetic chain of spins: stability of ferromagnetic and antiferromagnetic phases [8700-48]
M. V. Kostyuchenko, Yaroslavl State Technical Univ. (Russian Federation)

Macroscopic quantum effects in transmission of signals along the superconducting microwave slotline towards quantum transmission lines [8700-52]

SESSION 4 MICRO- AND NANOSCALE DEVICES

Terahertz-wave generation using graphene: toward the creation of graphene injection lasers [8700-21]
T. Otsuji, A. Satou, S. A. Boubanga Tombet, M. Ryzhii, V. Ryzhii, Tohoku Univ. (Japan)

Characterization and qualification of deep-submicron OTP poly-fuse memory [8700-42]
N. Belova, D. Allman, ON Semiconductor (United States); S. Tibbits, Jet City Electronics Inc. (United States)

Recording of information in nanostructures of transition metal silicides [8700-46]
A. S. Sigov, Moscow State Institute of Radiotechnics, Electronics and Automation (Russian Federation); B. M. Darinskii, Voronezh State Univ. (Russian Federation); L. A. Bilyutskaya, O. V. Ovchinnikov, M. S. Smirnov, M. V. Grechkina, Rosblovkant Ltd. (Russian Federation); A. P. Lazarev, Voronezh State Univ. (Russian Federation); G. A. Veligura, Research Institute of Electronic Technology (Russian Federation); A. V. Tuchin, E. V. Bogatikov, Voronezh State Univ. (Russian Federation)

A gold free fully copper metalized GaAs pHEMT for the high frequency applications [8700-9]
E. V. Erofeev, V. A. Kagadei, Micran (Russian Federation); A. I. Kazimirov, Tomsk State Univ. of Control Systems and Radioelectronics (Russian Federation)
8700 ON  **Noise characteristics of nanoscaled SOI MOSFETs** [8700-36]
N. Lukyanchikova, N. Garbar, V. Kudina, A. Smolanka, V. Lashkaryov Institute of Semiconductor Physics (Ukraine); E. Simoen, IMEC (Belgium); C. Claeys, IMEC (Belgium) and Katholieke Univ. Leuven (Belgium)

8700 0O  **Narrowing of nanogap for purpose of molecular single-electronics** [8700-25]
I. V. Sapkov, E. S. Soldatov, Moscow State Univ. (Russian Federation)

8700 0P  **The novel THz generation and detection possibilities of resonant-tunneling based semiconductor multiple-quantum well nanostructures** [8700-51]

8700 0Q  **Mechanism of sensitivity of a three-collector magnetotransistor** [8700-56]

---

**SESSION 5  MICROELECTROMECHANICAL SYSTEMS**

8700 0R  **Design and fabrication of piezoelectric MEMS** [8700-13]
N. Korobova, V. Vodopyanov, S. Timoshenkov, National Research Univ. of Electronic Technology (Russian Federation)

8700 0S  **Resonance properties of multilayer metallic nanocantilevers** [8700-2]
I. V. Uvarov, V. V. Naumov, I. I. Amirov, Institute of Physics and Technology, Yaroslavl Branch (Russian Federation)

8700 0T  **The mode matching technology for MEMS gyroscopes with mutually spaced eigenfrequencies** [8700-5]
O. Morozov, A. Postnikov, I. Kozin, Institute of Physics and Technology, Yaroslavl Branch (Russian Federation); A. Soloviev, A. Tarasov, Federal State Unitary Enterprise “Ctr. for Ground-Based Space Infrastructure Facilities Operation” (Russian Federation)

---

**SESSION 6  CHARACTERIZATION AND METROLOGY**

8700 0U  **Natural oxide thickness measurements on the test silicon relief pitch structure** [8700-24]
M. N. Filippov, Moscow Institute of Physics and Technology (Russian Federation) and Ctr. for Surface and Vacuum Research (Russian Federation); and Kurnakov Institute of General and Inorganic Chemistry (Russian Federation); M. A. Ermakova, V. P. Gavrilenko, A. A. Kuzin, Moscow Institute of Physics and Technology (Russian Federation) and Ctr. for Surface and Vacuum Research (Russian Federation); A. Yu. Kuzin, Ctr. for Surface and Vacuum Research (Russian Federation); A. A. Kuzmin, Moscow Institute of Physics and Technology (Russian Federation) and Ctr. for Surface and Vacuum Research (Russian Federation); V. B. Mityukhlyaev, A. V. Rakov, JSC Ctr. for Surface and Vacuum Research (Russian Federation); P. A. Todua, Moscow Institute of Physics and Technology (Russian Federation) and Ctr. for Surface and Vacuum Research (Russian Federation); A. V. Zablotskiy, Moscow Institute of Physics and Technology (Russian Federation) and Ctr. for Surface and Vacuum Research (Russian Federation)
Determining the state of non-volatile memory cells with floating gate using scanning probe microscopy [8700-30]

D. Hanzii, Institute of Nanotechnology of Microelectronics (Russian Federation); E. Kelm, N. Luapunov, R. Milovanov, G. Molodcova, NT-MDT (Russian Federation); M. Yanul, Institute of Nanotechnology of Microelectronics (Russian Federation); D. Zubov, NT-MDT (Russian Federation)

Mechanisms of image formation in SEM [8700-7]

Y. V. Larionov, Y. A. Novikov, A. M. Prokhorov General Physics Institute (Russian Federation)

Virtual scanning electron microscope [8700-15]

Y. V. Larionov, Y. A. Novikov, A. M. Prokhorov General Physics Institute (Russian Federation)

Effective probe for scanning electron microscope [8700-10]

Y. V. Larionov, Y. A. Novikov, A. M. Prokhorov General Physics Institute (Russian Federation)

Detection of processes inducing profile changes of relief structures in SEM by analysis of their distorted images [8700-18]

Y. V. Larionov, Y. A. Novikov, A. M. Prokhorov General Physics Institute (Russian Federation)

Atomic force microscopy for line edge roughness measurements [8700-41]

A. Y. Sosnina, Institute of Physics and Technology (Russian Federation) and Moscow Institute of Physics and Technology (Russian Federation); A. E. Rogozhin, A. V. Miakonkikh, Institute of Physics and Technology (Russian Federation)

SESSION 7 SIMULATION AND MODELING

Ionization energy oscillations in metallic and semiconducting nanotubes of ultra small diameters [8700-20]

E. N. Bormontov, A. A. Ganin, L. A. Bilyutskaya, Voronezh State Univ. (Russian Federation)

Computationally efficient method for optical simulation of solar cells and their applications [8700-29]

I. Semenikhin, Institute of Physics and Technology (Russian Federation); M. Zanuccoli, C. Fiegna, Univ. degli Studi di Bologna (Italy); V. Vyurkov, Institute of Physics and Technology (Russian Federation); E. Sangiorgi, Univ. degli Studi di Bologna (Italy)

Simulation of resonant tunneling devices based on different materials [8700-4]

I. I. Abramov, N. V. Kolomejseva, I. A. Romanova, A. G. Klimovich, Belarusian State Univ. of Informatics and Radioelectronics (Belarus)

A universal model for single-electron device simulation [8700-3]

I. I. Abramov, A. L. Baranoff, I. A. Romanova, I. Y. Shcherbakova, Belarusian State Univ. of Informatics and Radioelectronics (Belarus)

Gold nanoparticle single-electron transistor simulation [8700-23]

Y. S. Gerasimov, Moscow State Univ. (Russian Federation) and National Research Ctr. Kurchatov Institute (Russian Federation); V. V. Shorokhov, E. S. Soldatov, Moscow State Univ. (Russian Federation); O. V. Snigirev, Moscow State Univ. (Russian Federation) and National Research Ctr. Kurchatov Institute (Russian Federation)
TCAD analysis of self-heating effects in bulk silicon and SOI n-MOSFETs [8700-43]
K. O. Petrosyants, Moscow Institute of Electronics and Mathematics of National Research Univ. (Russian Federation); E. V. Orekhov, Institute for Design Problems in Microelectronics (Russian Federation); I. A. Kharitonov, D. A. Popov, Moscow Institute of Electronics and Mathematics of National Research Univ. (Russian Federation)

Numerical model of parallel nano-FET on Coulomb blockade in Mss "magic" crystals [8700-34]
V. A. Zhukov, St. Petersburg Institute for Informatics and Automation (Russian Federation); V. G. Maslov, St. Petersburg National Research Univ. of Information Technologies, Mechanics and Optics (Russian Federation)

Capacitance properties of MOS capacitors with oxide-hosted Si nanoparticles [8700-12]
V. A. Stuchinsky, G. N. Kamaev, M. D. Efremov, S. A. Arzhannikova, A.V. Rzhanov Institute of Semiconductor Physics (Russian Federation)

SESSION 8 QUANTUM INFORMATICS

Mathematical models of quantum noise [8700-37]
Y. I. Bogdanov, Institute of Physics and Technology (Russian Federation); A. Y. Chernyavskiy, Institute of Physics and Technology (Russian Federation) and Moscow State Univ. (Russian Federation); A. S. Holevo, Steklov Mathematical Institute (Russian Federation); V. F. Lukichev, A. A. Orlikovsky, Institute of Physics and Technology (Russian Federation)

Modeling of quantum noise and the quality of hardware components of quantum computers [8700-38]
Y. I. Bogdanov, Institute of Physics and Technology (Russian Federation); A. Y. Chernyavskiy, Institute of Physics and Technology (Russian Federation) and Moscow State Univ. (Russian Federation); A. Holevo, Steklov Mathematical Institute (Russian Federation); V. F. Lukichev, A. A. Orlikovsky, Institute of Physics and Technology (Russian Federation)

Creating, maintaining, and breaking of quantum entanglement in quantum operations [8700-39]
Y. I. Bogdanov, Institute of Physics and Technology (Russian Federation); A. Y. Chernyavskiy, Institute of Physics and Technology (Russian Federation) and Moscow State Univ. (Russian Federation); A. S. Holevo, Steklov Mathematical Institute (Russian Federation); V. F. Lukichev, A. A. Orlikovsky, Institute of Physics and Technology (Russian Federation); B. I. Bantysh, National Research Univ. of Electronic Technology MIET (Russian Federation)
8700 1C Mathematical modeling and experimental study of polarization echo in optically anisotropic media [8700-47]
Y. I. Bogdanov, Institute of Physics and Technology (Russian Federation); A. A. Kalinkin, Moscow State Univ. (Russian Federation) and Zavoisky Physical-Technical Institute (Russian Federation); S. P. Kulik, Moscow State Univ. (Russian Federation); E. V. Moreva, Moscow State Univ. (Russian Federation) and National Research Nuclear Univ. MEPhi (Russian Federation); V. A. Shershulin, Institute of Physics and Technology (Russian Federation) and Moscow State Univ. (Russian Federation) and National Research Univ. of Electronic Technology MIET (Russian Federation); L. V. Belinsky, Institute of Physics and Technology (Russian Federation) and National Research Univ. of Electronic Technology MIET (Russian Federation)

8700 1D Quantum and classical correlations in high temperature dynamics of two coupled large spins [8700-16]
V. E. Zobov, Kirensky Institute of Physics (Russian Federation)

8700 1E Quantum information transfer between two-component Bose-Einstein condensates connected by optical fiber [8700-26]
A. N. Pyrkov, T. Byrnes, National Institute of Informatics (Japan)

8700 1F Quantum register based on structured diamond waveguide with NV centers [8700-50]
A. V. Tsukanov, I. Y. Kateev, A. A. Orlikovsky, Institute of Physics and Technology (Russian Federation)

8700 1G On the time-optimal implementation of quantum Fourier transform for qudits represented by quadrupole nucleus [8700-17]
V. P. Shauro, V. E. Zobov, Kirensky Institute of Physics (Russian Federation)

8700 1H Measure of decoherence in quantum error correction for solid-state quantum computing [8700-1]
A. A. Melnikov, Institute of Physics and Technology (Russian Federation) and Moscow Institute of Physics and Technology (Russian Federation); L. E. Fedichkin, Institute of Physics and Technology (Russian Federation) and Moscow Institute of Physics and Technology (Russian Federation) and NIX (Russian Federation)

Author Index
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Plasma and Ion Beam Technologies I  
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Quantum Informatics VII  
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Plasma and Ion Beam Technologies II  
**Alexander M. Efremov**, Ivanovo State University of Chemistry and Technology (Russian Federation)
Introduction

The volume contains selected papers presented at the International Conference "Micro- and Nanoelectronics 2012" (ICMNE-2012) which has been held in Zvenigorod, Moscow Region, Russia during October 1-5, 2012. ICMNE is a biannual conference covering the main fields of micro- and nanoelectronic technologies and device physics. Since 1992 the Institute of Physics and Technology of the Russian Academy of Sciences is the permanent organizer of ICMNE. From 2003 ICMNE is an SPIE-affiliated conference.

ICMNE-2012 included the Extended Session "Quantum Informatics-2012" and the Workshop "Silicon-on-Insulator-2012". The ICMNE-2012 scope contained such scientific and technological fields as micro- and nanoelectronic materials and films, technologies and equipment, metrology, physics and technologies of micro- and nanodevices, simulation and modeling, silicon-on-insulator and low-dimensional structures, quantum informatics. ICMNE-2012 included three plenary sessions and 21 topical sessions covering the following areas of focus:

- Advanced Lithography
- Magnetic Micro- and Nanostructures
- Metrology and Characterization
- Micro- and Nanodevices
- Micro- and Nanoelectromechanical Systems
- Micro- and Nanoelectronic Structures
- Plasma and Ion Beam Technologies
- Quantum Informatics
- Silicon-on-Insulator
- Simulation and Modeling
- Superconducting Structures and Devices

The scientific program was based on invited and contributed papers from the scientists employed at European and Siberian Regions of Russia, Ukraine, Belarus, United Kingdom, France, United States, Japan, and Korea. The invited lectures on the current achievements and challenges in the contemporary microelectronics were delivered by the scientists from France, Belgium, Germany, Japan, Australia, and Russia. The contributions to the sessions of the Conference were made by academic institutions, universities as well as from the industry. More than 120 contributions were discussed at oral presentations; about 120 others were presented as posters.

We hope that helpful discussions of these works at the sessions of the Conference and during personal contacts between attendees will promote the research
activity in microelectronic community. Additional information about ICMNE-2012 can be found at the conference website http://www.icmne.ftian.ru

Alexander A. Orlikovsky